

Dual N-Channel Enhancement Mode MOSFET

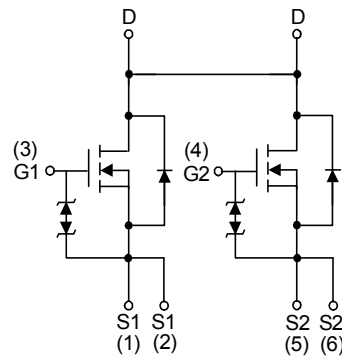
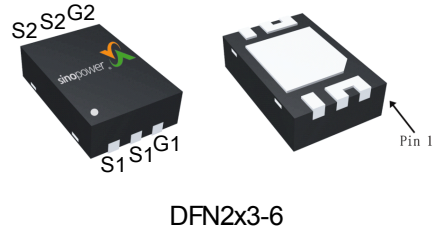
Features

- 20V/12A,
 $R_{DS(ON)} = 7.4m\Omega$ (Max.) @ $V_{GS} = 4.5V$
 $R_{DS(ON)} = 7.6m\Omega$ (Max.) @ $V_{GS} = 4V$
 $R_{DS(ON)} = 8m\Omega$ (Max.) @ $V_{GS} = 3.7V$
 $R_{DS(ON)} = 8.7m\Omega$ (Max.) @ $V_{GS} = 3.1V$
 $R_{DS(ON)} = 10m\Omega$ (Max.) @ $V_{GS} = 2.5V$
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)
- ESD protection

Applications

- Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems.
- One Cell Li-ion Battery Pack.

Pin Description



N-Channel MOSFET

Ordering and Marking Information

<p>SM9993DS □□□-□□□</p> <ul style="list-style-type: none"> □□□□ - Assembly Material □□□□ - Handling Code □□□□ - Temperature Range □□□□ - Package Code 	<p>Package Code QG : DFN3x2-6 Operating Junction Temperature Range C : -55 to 150 °C Handling Code TR : Tape & Reel (3000ea/reel) Assembly Material G : Halogen and Lead Free Device</p>
<p>SM9993DS QG : 9993 XXXX</p>	<p>XXXX - Lot Code</p>

Note: SINOPOWER lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish; which are fully compliant with RoHS. SINOPOWER lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J-STD-020D for MSL classification at lead-free peak reflow temperature. SINOPOWER defines "Green" to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

SINOPOWER reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Rating	Unit	
Common Ratings				
V_{DSS}	Drain-Source Voltage	20	V	
V_{GSS}	Gate-Source Voltage	± 12		
I_D	Continuous Drain Current	$T_A=25^\circ\text{C}$	12	A
		$T_A=70^\circ\text{C}$	9	
I_{DM}	Continuous Drain Current	$T_A=25^\circ\text{C}$	18^b	A
I_S	Diode Continuous Forward Current	1	A	
T_J	Maximum Junction Temperature	150	$^\circ\text{C}$	
T_{STG}	Storage Temperature Range	-55 to 150		
P_D	Maximum Power Dissipation	$T_A=25^\circ\text{C}$	1.56	W
		$T_A=70^\circ\text{C}$	1.0	
$R_{\theta JA}^a$	Thermal Resistance-Junction to Ambient	$t \leq 10\text{s}$	80	$^\circ\text{C/W}$

Note a : Surface Mounted on 1in^2 pad area, $t \leq 10\text{sec}$.

Note b : Current limited by bond wire.

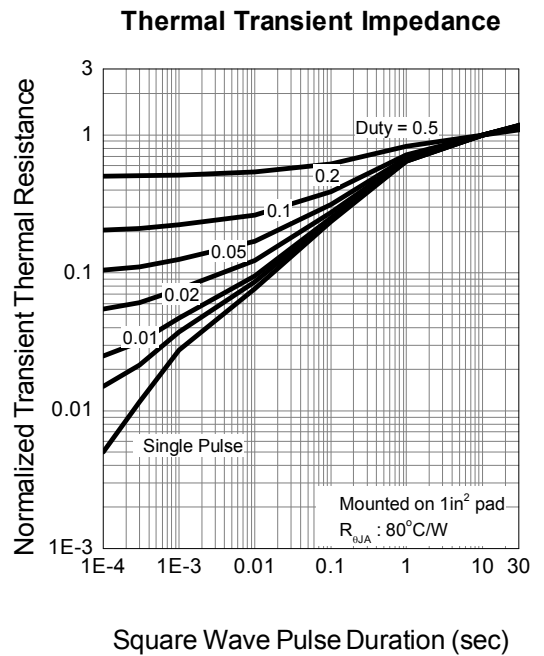
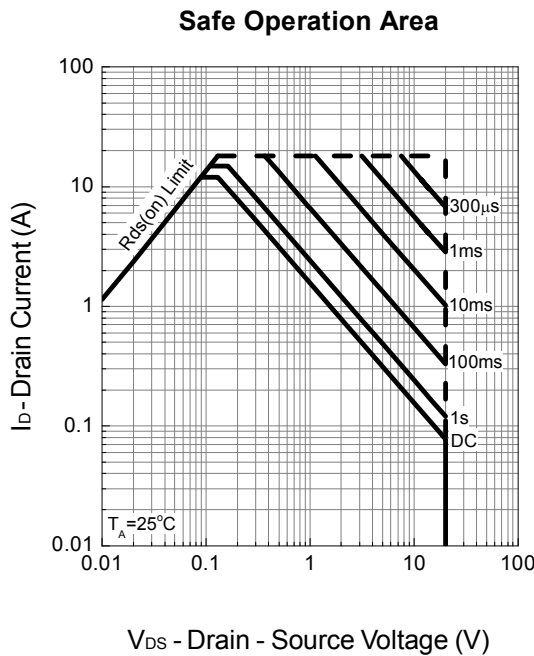
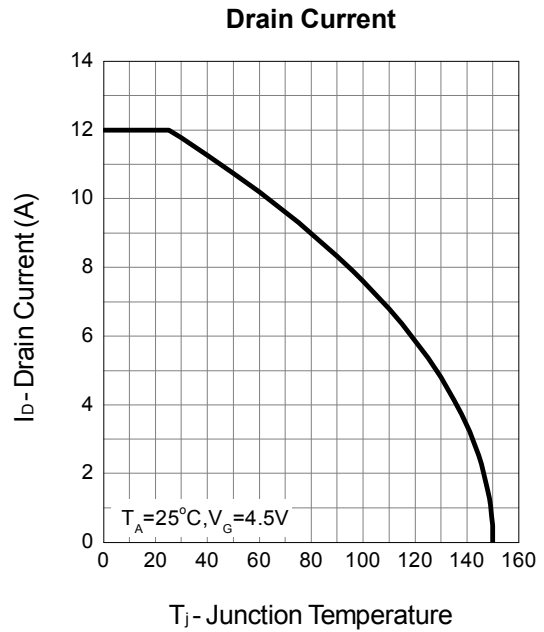
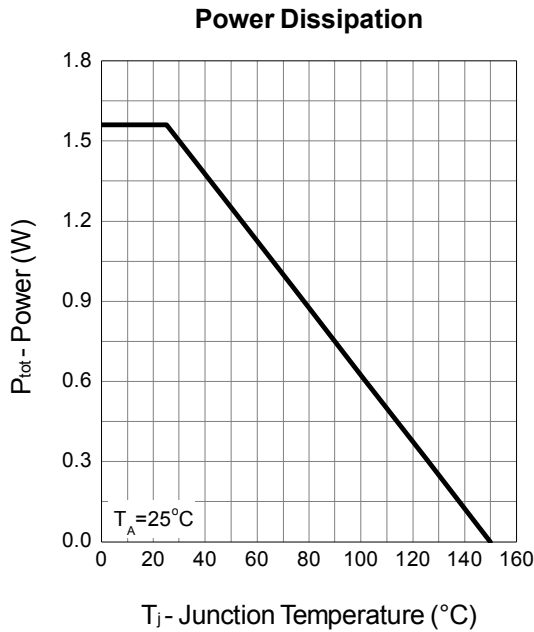
Electrical Characteristics ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu A$	20	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=16V, V_{GS}=0V$	-	-	1	μA
		$T_J=85^\circ C$	-	-	30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	0.5	0.7	1	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	± 10	μA
$R_{DS(on)}^c$	Drain-Source On-state Resistance	$V_{GS}=4.5V, I_{DS}=5.5A$	4.7	6.2	7.4	$m\Omega$
		$V_{GS}=4V, I_{DS}=5.5A$	4.8	6.3	7.6	$m\Omega$
		$V_{GS}=3.7V, I_{DS}=5.5A$	4.9	6.4	8	$m\Omega$
		$V_{GS}=3.1V, I_{DS}=5.5A$	5.0	6.8	8.7	$m\Omega$
		$V_{GS}=2.5V, I_{DS}=5.5A$	5.8	8.0	10	$m\Omega$
Diode Characteristics						
V_{SD}^c	Diode Forward Voltage	$I_{SD}=1A, V_{GS}=0V$	-	0.7	1.3	V
Dynamic Characteristics^d						
R_G	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, f=1MHz$	-	2.3	-	Ω
C_{iss}	Input Capacitance	$V_{GS}=0V, V_{DS}=10V, \text{Frequency}=1.0MHz$	-	1750	-	pF
C_{oss}	Output Capacitance					
C_{rss}	Reverse Transfer Capacitance					
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=10V, R_L=10\Omega, I_{DS}=1A, V_{GEN}=10V, R_G=6\Omega$	-	8	14.5	ns
t_r	Turn-on Rise Time					
$t_{d(OFF)}$	Turn-off Delay Time					
t_f	Turn-off Fall Time					
Gate Charge Characteristics^d						
Q_g	Total Gate Charge	$V_{DS}=10V, V_{GS}=4.5V, I_{DS}=5.5A$	-	16	-	nC
Q_{gs}	Gate-Source Charge					
Q_{gd}	Gate-Drain Charge					

Note c : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

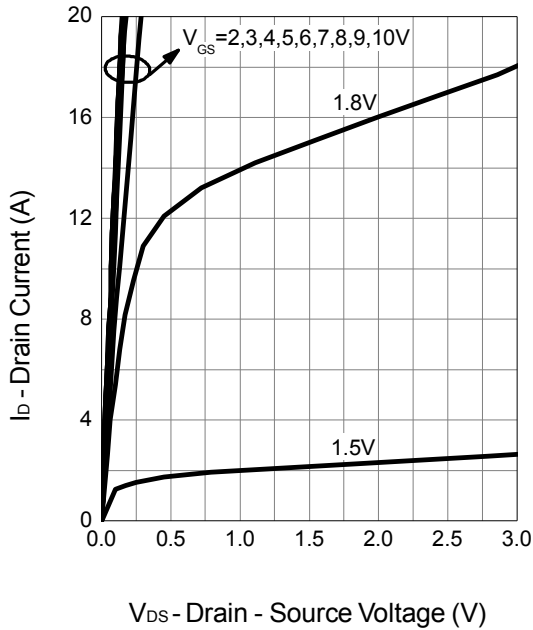
Note d : Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

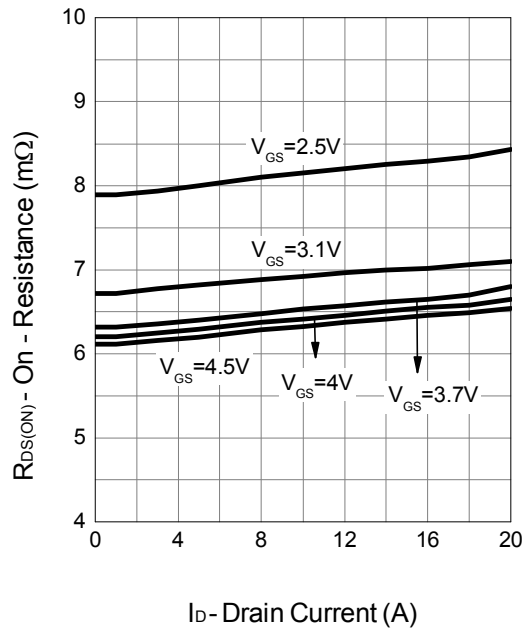


Typical Operating Characteristics (Cont.)

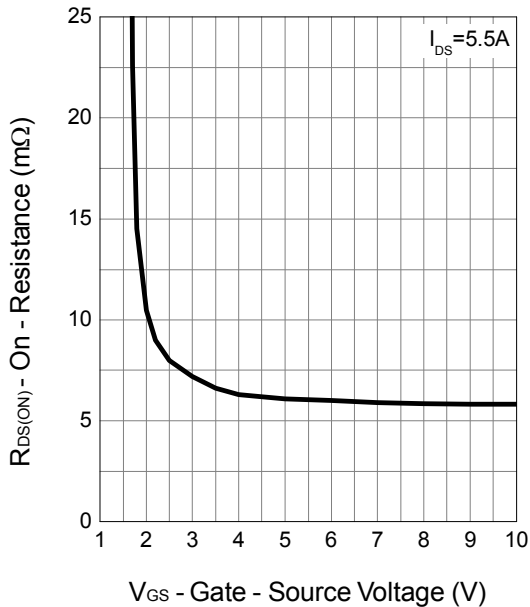
Output Characteristics



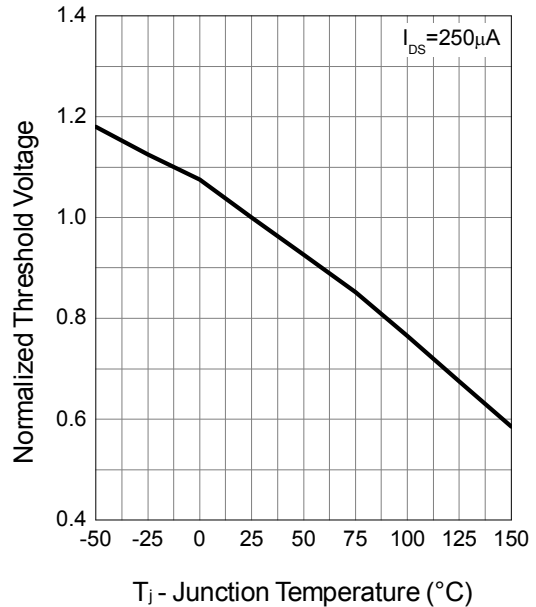
Drain-Source On Resistance



Gate-Source On Resistance

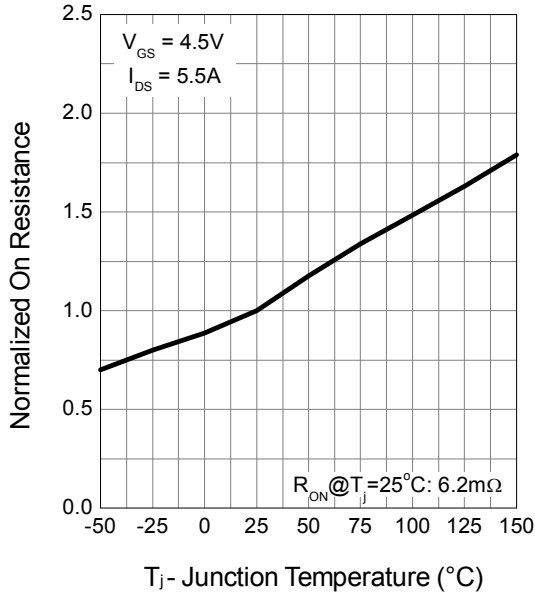


Gate Threshold Voltage

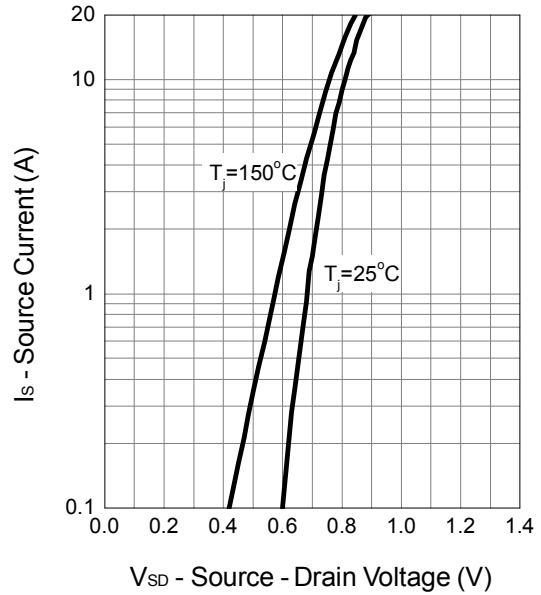


Typical Operating Characteristics (Cont.)

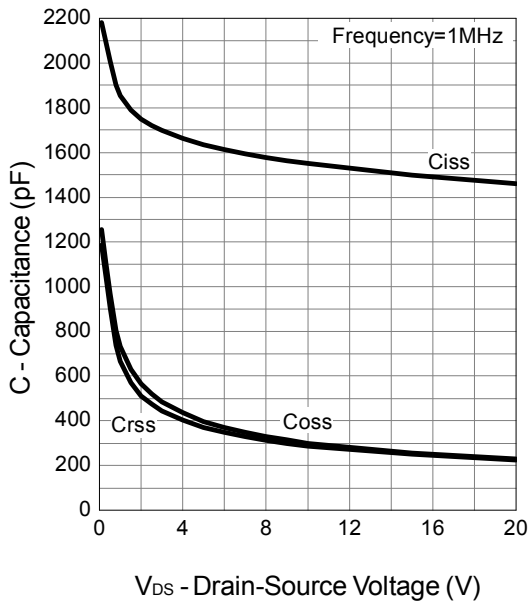
Drain-Source On Resistance



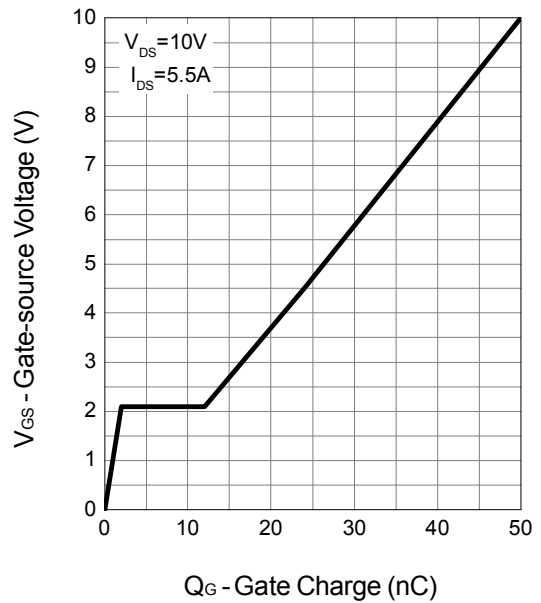
Source-Drain Diode Forward



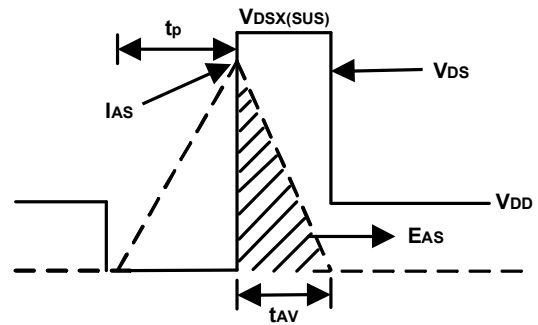
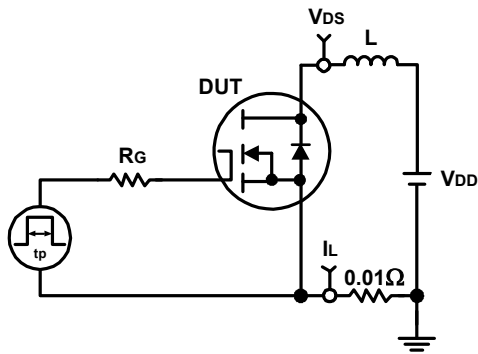
Capacitance



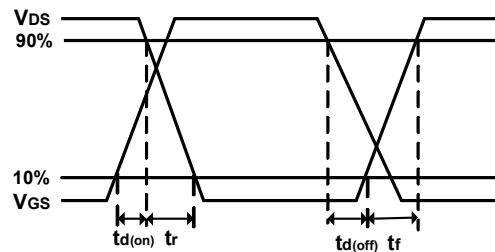
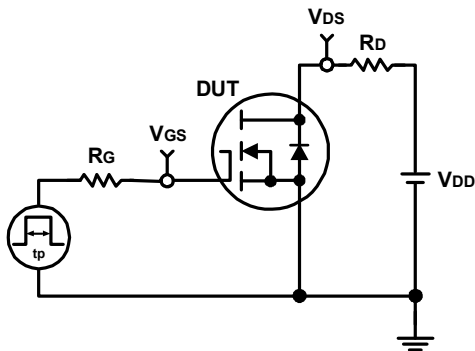
Gate Charge



Avalanche Test Circuit and Waveforms

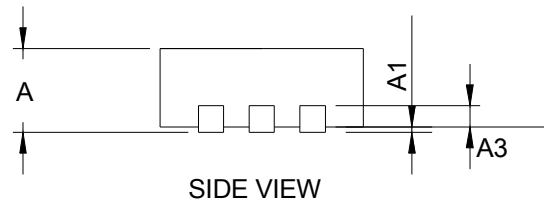
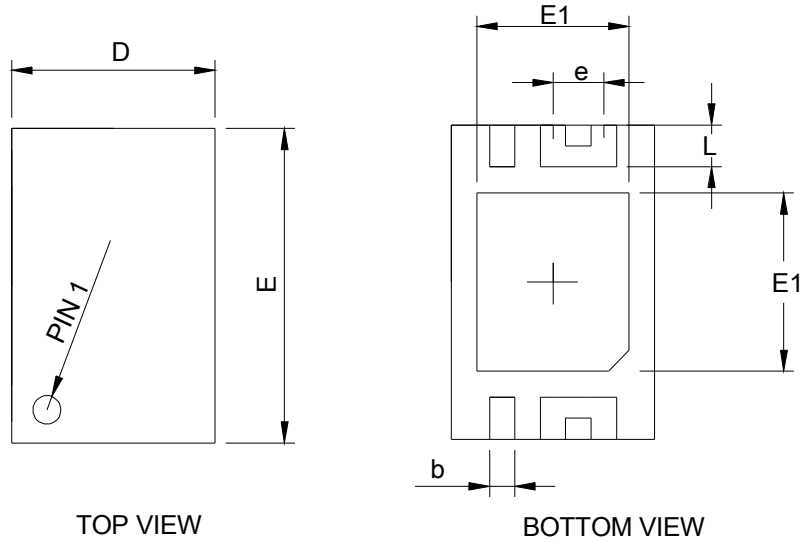


Switching Time Test Circuit and Waveforms



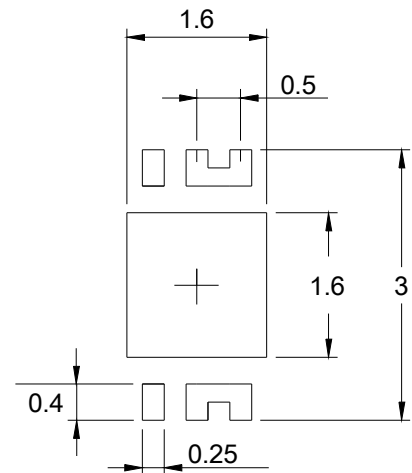
Package Information

DFN2x3-6 (saw type)



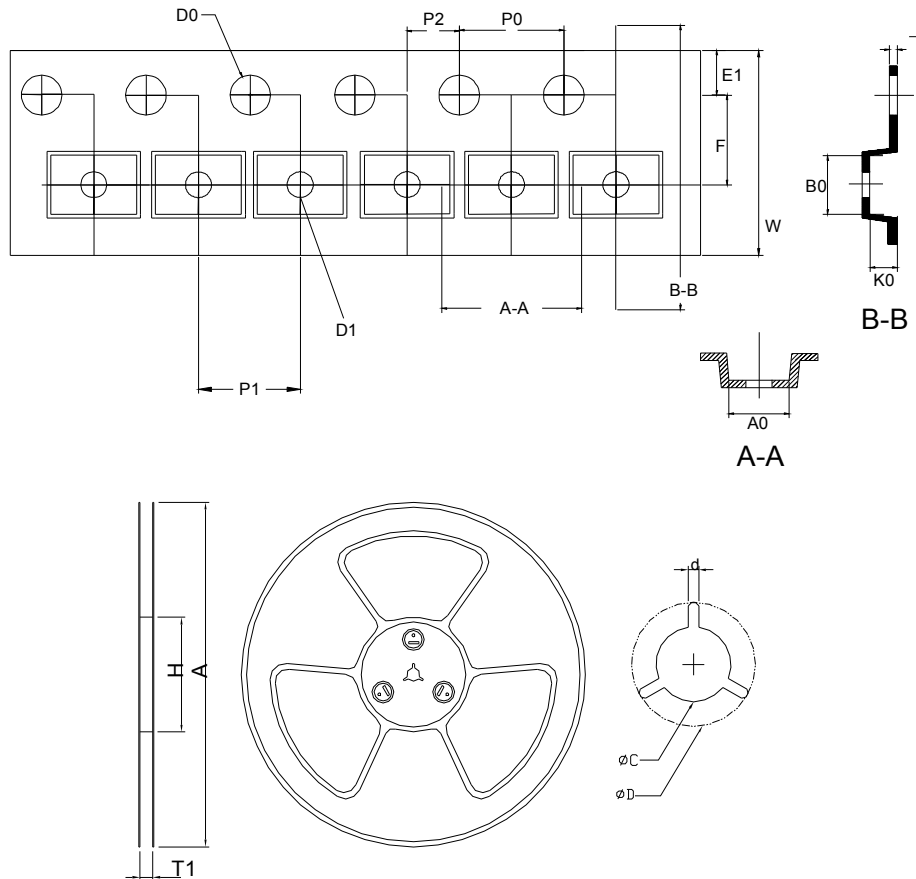
SYMBOL	DFN2x3-6			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.70	1.00	0.028	0.039
A1	0.00	0.05	0.000	0.002
A3	0.203 REF		0.008 REF	
b	0.20	0.30	0.008	0.012
D	1.90	2.10	0.075	0.083
E1	1.60	1.80	0.063	0.071
E	2.90	3.10	0.114	0.122
D1	1.40	1.60	0.055	0.063
e	0.50 BSC		0.02 BSC	
L	0.30	0.50	0.012	0.020

RECOMMENDED LAND PATTERN



UNIT: mm

Carrier Tape & Reel Dimensions

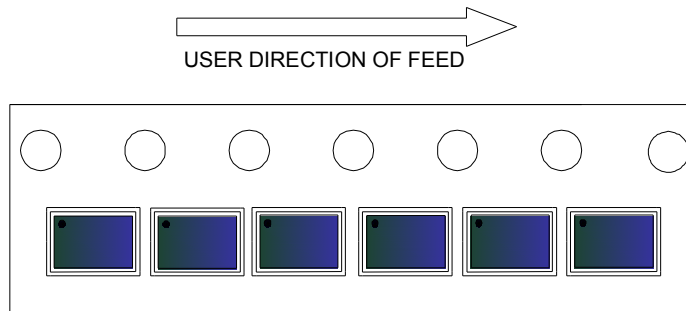


Application	A	H	T1	C	d	D	W	E1	F
DFN2x3-6 (saw type)	178.0±2.00	50 MIN.	8.4+2.50 -0.00	13.0+0.50 -0.20	1.5 MIN.	20.2 MIN.	8.0±0.30	1.75±0.10	3.5±0.05
	P0	P1	P2	D0	D1	T	A0	B0	K0
	4.0±0.10	4.0±0.10	2.0±0.05	1.5+0.10 -0.00	1.0 MIN.	0.254±0.02	3.29±0.10	2.31±0.10	1.10±0.10

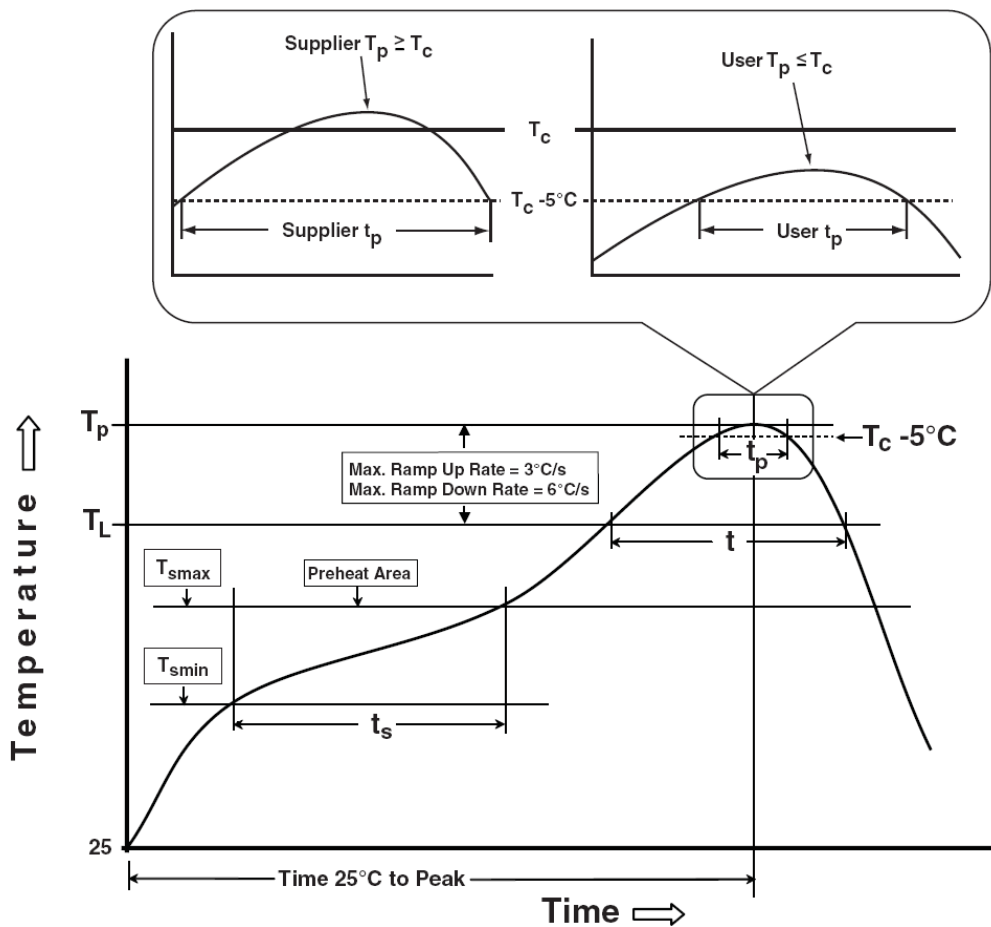
(mm)

Taping Direction Information

DFN2x3-6



Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T_{smin})	100 °C	150 °C
Temperature max (T_{smax})	150 °C	200 °C
Time (T_{smin} to T_{smax}) (t_s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L)	183 °C	217 °C
Time at liquidous (t_L)	60-150 seconds	60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_p)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum. ** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HTRB	JESD-22, A108	1000 Hrs, 80% of VDS max @ T_{jmax}
HTGB	JESD-22, A108	1000 Hrs, 100% of VGS max @ T_{jmax}
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -65°C~150°C

Customer Service

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